P-Channel 60-V (D-S) MOSFET

Key Features:

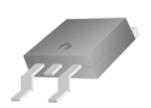
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

| Tv | pical | Apı | plications | :: |
|-----|---------|------|------------|----|
| - 7 | | , .L | p a | - |

- Load Switches
- DC/DC Conversion
- Motor Drives

| PRODUCT SUMMARY | | | | |
|---------------------|-----------------------------|-------|--|--|
| V _{DS} (V) | $r_{DS(on)}(m\Omega)$ | I⊳(A) | | |
| -60 | 22 @ V _{GS} = -10V | -39 | | |
| | $28 @ V_{GS} = -4.5V$ | -35 | | |







| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) | | | | | | |
|---|----------------------|-----------------|------------|-------|--|--|
| Parameter | | Symbol | Limit | Units | | |
| Drain-Source Voltage | | | -60 | V | | |
| Gate-Source Voltage | | V_{GS} | ±20 | V | | |
| Continuous Drain Current ^a | T _C =25°C | I_D | -39 | Α | | |
| Pulsed Drain Current ^b | | I _{DM} | -160 | ζ | | |
| Continuous Source Current (Diode Conduction) ^a | | I _S | -39 | Α | | |
| Power Dissipation ^a | T _C =25°C | P_{D} | 50 | W | | |
| Operating Junction and Storage Temperature Range | · | T_J, T_{stg} | -55 to 175 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|-----------------|---------|-------|--|--|
| Parameter | Symbol | Maximum | Units | | |
| Maximum Junction-to-Ambient ^a | $R_{\theta JA}$ | 40 | °C/W | | |
| Maximum Junction-to-Case | $R_{\theta JC}$ | 3 | C/VV | | |

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

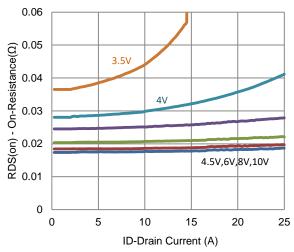
| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit |
|---|---------------------|---|-----|------|------|-------|
| Static | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$ | -1 | | | V |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA |
| Zara Cata Valtaria Drain Comment | 1 | $V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$ | | | -1 | uA |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | -10 | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$ | -60 | | | Α |
| Drain Course On Besistenes a | r | $V_{GS} = -10 \text{ V}, I_{D} = -20 \text{ A}$ | | | 22 | mΩ |
| Drain-Source On-Resistance ^a | r _{DS(on)} | $V_{GS} = -4.5 \text{ V}, I_{D} = -16 \text{ A}$ | | | 28 | 11122 |
| Forward Transconductance a | g _{fs} | $V_{DS} = -15 \text{ V}, I_{D} = -20 \text{ A}$ | | 38 | | S |
| Diode Forward Voltage ^a | V_{SD} | $I_{S} = -20 \text{ A}, V_{GS} = 0 \text{ V}$ | | -0.9 | | V |
| | | Dynamic ^b | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$ | | 40 | | |
| Gate-Source Charge | Q_gs | $I_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -20 \text{ A}$ | | 18 | | nC |
| Gate-Drain Charge | Q_gd | 10 = 20 A | | 13 | | |
| Turn-On Delay Time | t _{d(on)} | $V_{DS} = -30 \text{ V}, R_1 = 1.5 \Omega,$ | | 10 | | |
| Rise Time | t _r | $I_{DS} = -30 \text{ V}, \text{ NL} = 1.3 \Omega,$ $I_{D} = -20 \text{ A},$ | | 10 | | ns |
| Turn-Off Delay Time | t _{d(off)} | $V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$ | | 100 | | 113 |
| Fall Time | t _f | VGEN - 10 V, NGEN 0 12 | | 32 | | |
| Input Capacitance | C _{iss} | | | 3536 | | |
| Output Capacitance | C _{oss} | $V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$ | | 227 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 168 | | |

Notes

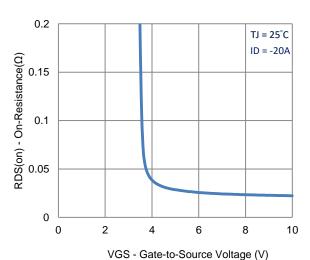
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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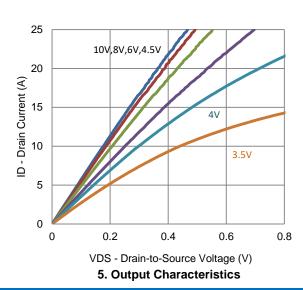
Typical Electrical Characteristics

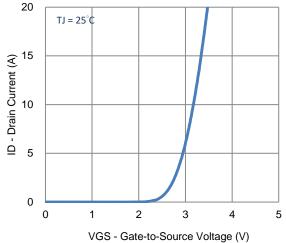


1. On-Resistance vs. Drain Current

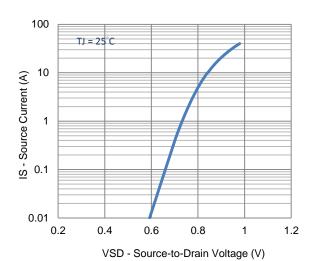


3. On-Resistance vs. Gate-to-Source Voltage

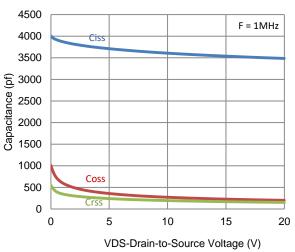




2. Transfer Characteristics

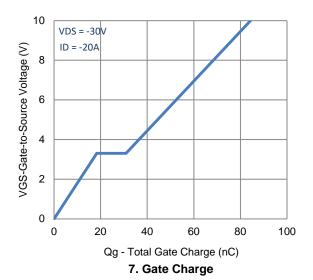


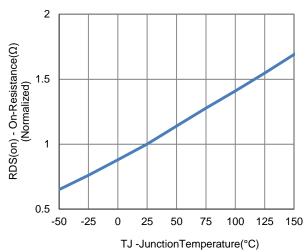
4. Drain-to-Source Forward Voltage



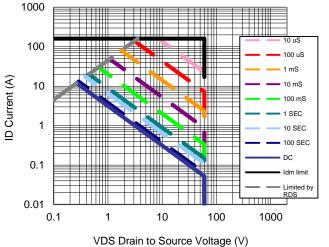
6. Capacitance

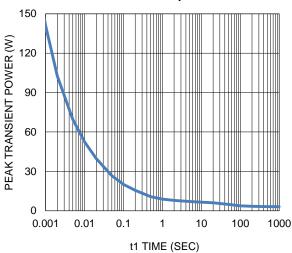
Typical Electrical Characteristics





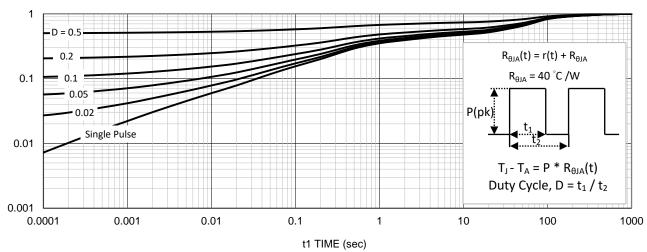
8. Normalized On-Resistance Vs Junction Temperature





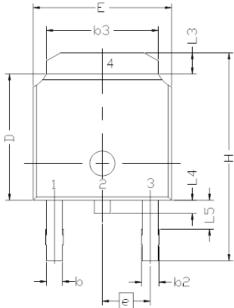
9. Safe Operating Area

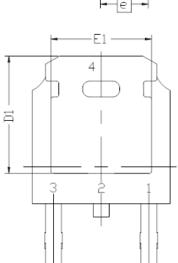
10. Single Pulse Maximum Power Dissipation



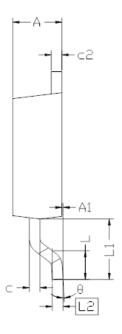
11. Normalized Thermal Transient Junction to Ambient

Package Information





SINGLE ROWNEW



| CVADDI | DIMENS: | IONAL F | REQMTS |
|--------|---------|---------|--------|
| SYMBOL | MIN | NDM | MAX |
| E | 6.40 | 6.60 | 6.731 |
| L | 1.40 | 1.52 | 1.77 |
| L1 | | .743 RI | |
| | 0. | .508 BS | _ |
| L3 | 0.89 | | 1.27 |
| L4 | 0.64 | | 1.01 |
| L5 | | | |
| D | 6.00 | 6.10 | 6.223 |
| Н | 9.40 | 10.00 | 10.40 |
| b | 0.64 | 0.76 | 0.88 |
| b2 | 0.77 | 0.84 | 1.14 |
| b3 | 5.21 | 5.34 | 5.46 |
| е | 2. | 286 BS | C |
| Α | 2.20 | 2.30 | 2,38 |
| A1 | 0 | | 0.127 |
| _ | 0.45 | 0.50 | 0.60 |
| c2 | 0.45 | 0.50 | 0,58 |
| D1 | 5,30 | | |
| E1 | 4.40 | | |
| θ | 0° | | 10° |

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.